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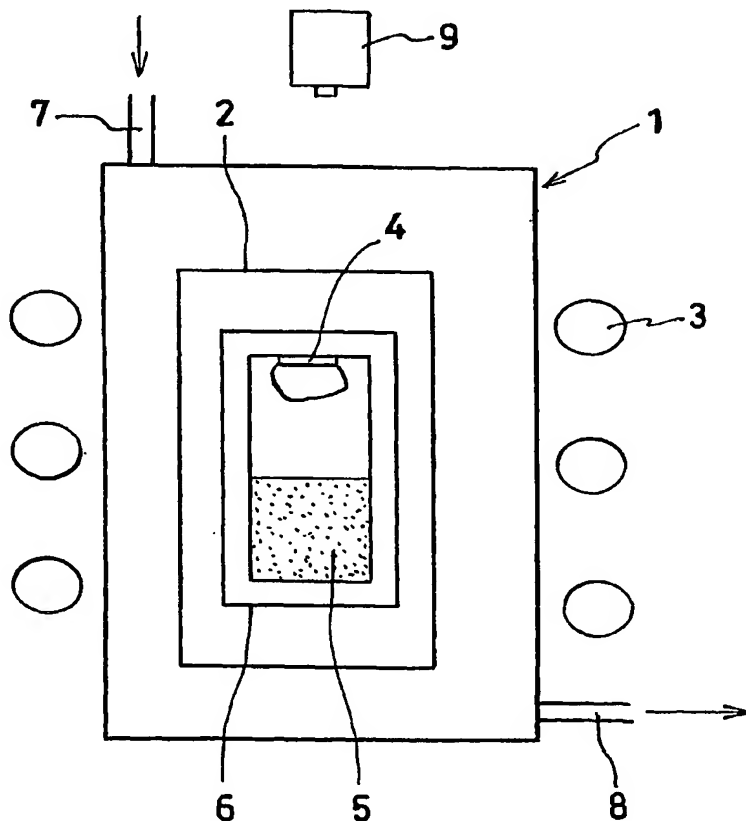
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(54) Title: METHOD FOR GROWTH OF SILICON CARBIDE SINGLE CRYSTAL, SILICON CARBIDE SEED CRYSTAL, AND SILICON CARBIDE SINGLE CRYSTAL



(57) Abstract: This invention relates to a method for crystal growth, particularly for the growth of high-quality single crystal in making crystal growth by the sublimation technique of a silicon carbide single crystal substrate to be used in optical devices and high pressure resistant, large-power semiconductor devices. This invention is a method for producing a single crystal including supplying a vapor gas from silicon carbide as a raw material to a seed crystal formed of a silicon carbide single crystal to the seed crystal. The seed crystal is disposed in a part of crystal growth, with a crystal face of the seed crystal inclined relative to a (0001) plane or (000-1) plane, thereby making crystal growth.

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